

The MOSFET Amplifier (1)

Lecture 7
October 4th, 2018

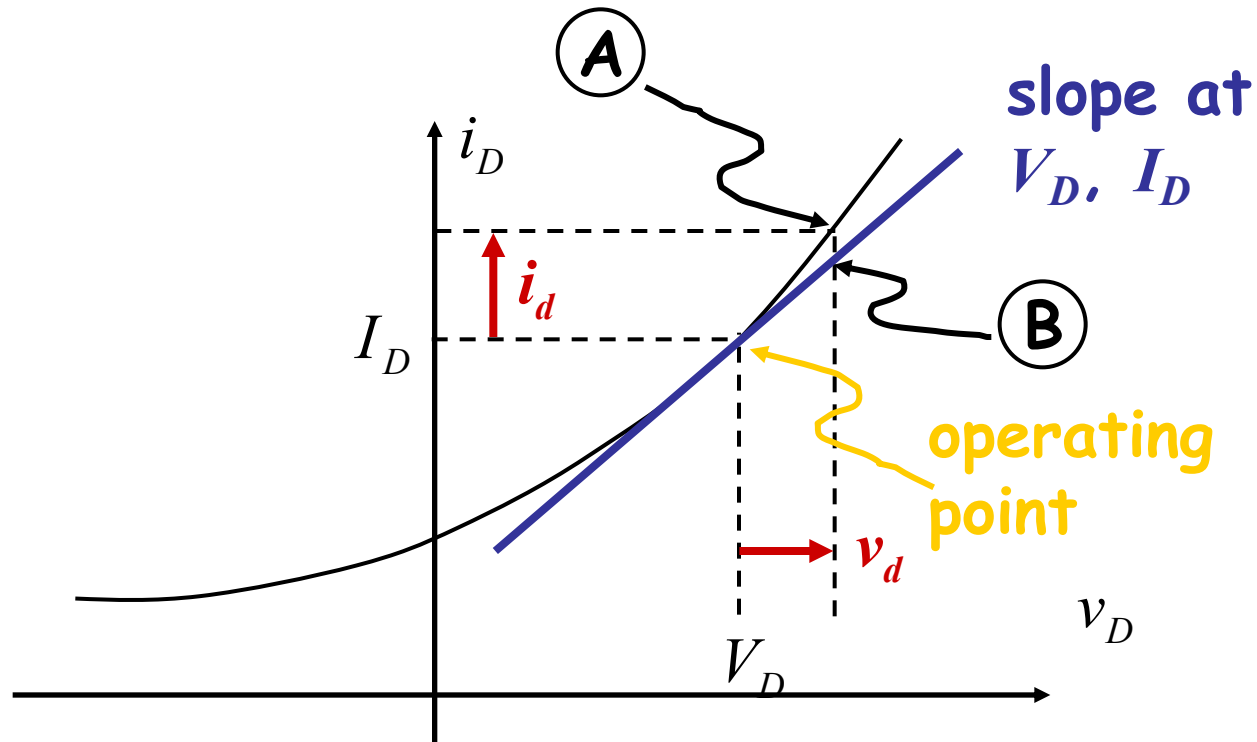
Jae W. Lee (jaewlee@snu.ac.kr)
Computer Science and Engineering
Seoul National University

Slide credits: Prof. Anant Agarwal at MIT

Review

■ Nonlinear circuits

- We can use the node method (or others) with nonlinear equations.
- Incremental analysis “**linearizes**” the circuit for small signals.



We are approximating (A) with (B)!

Outline

Textbook: 7.1, 7.2, 7.3, 7.4

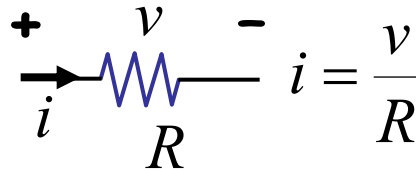
- **(Review of) Dependent Sources**
- Why Amplify?
- Signal Amplification
- Actual MOSFET Characteristics
- MOSFET SCS Model

Dependent Sources

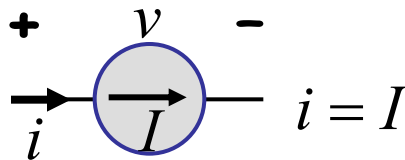
■ Independent source

Seen previously

Resistor

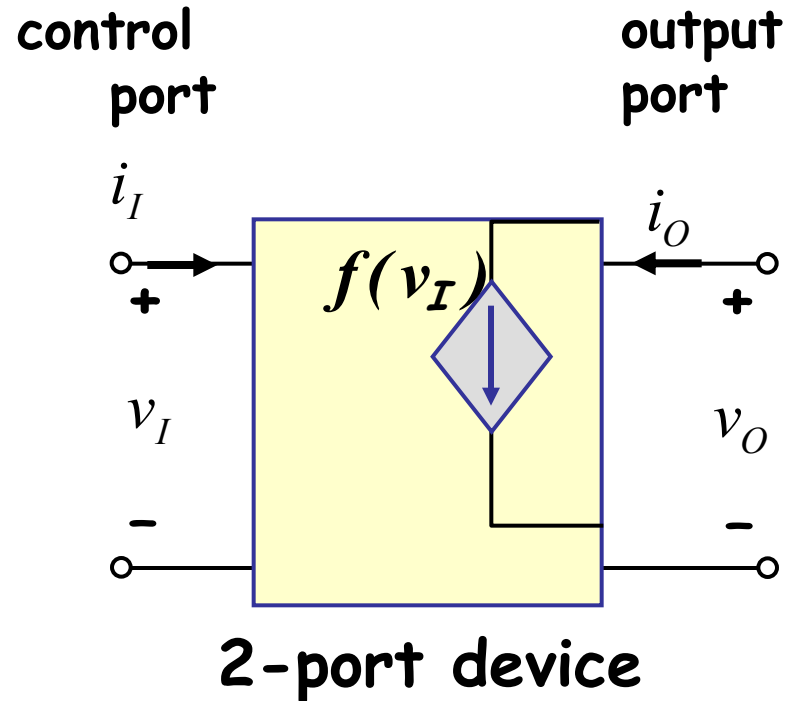


Independent
Current source



2-terminal 1-port devices

■ Dependent source

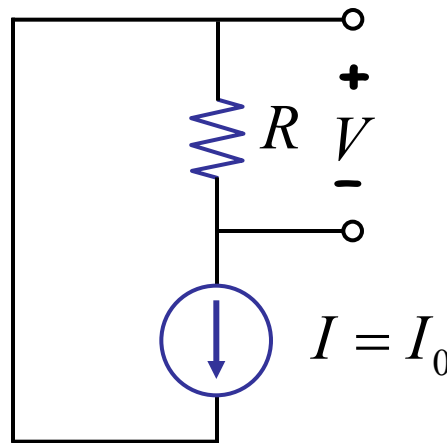


e.g., Voltage Ctrl'd Current Source
Current at output port is a function of
voltage at the input port

Dependent Sources

■ Example 1 (independent source): Find V

independent
current
source

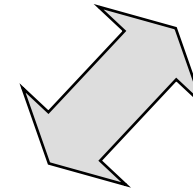
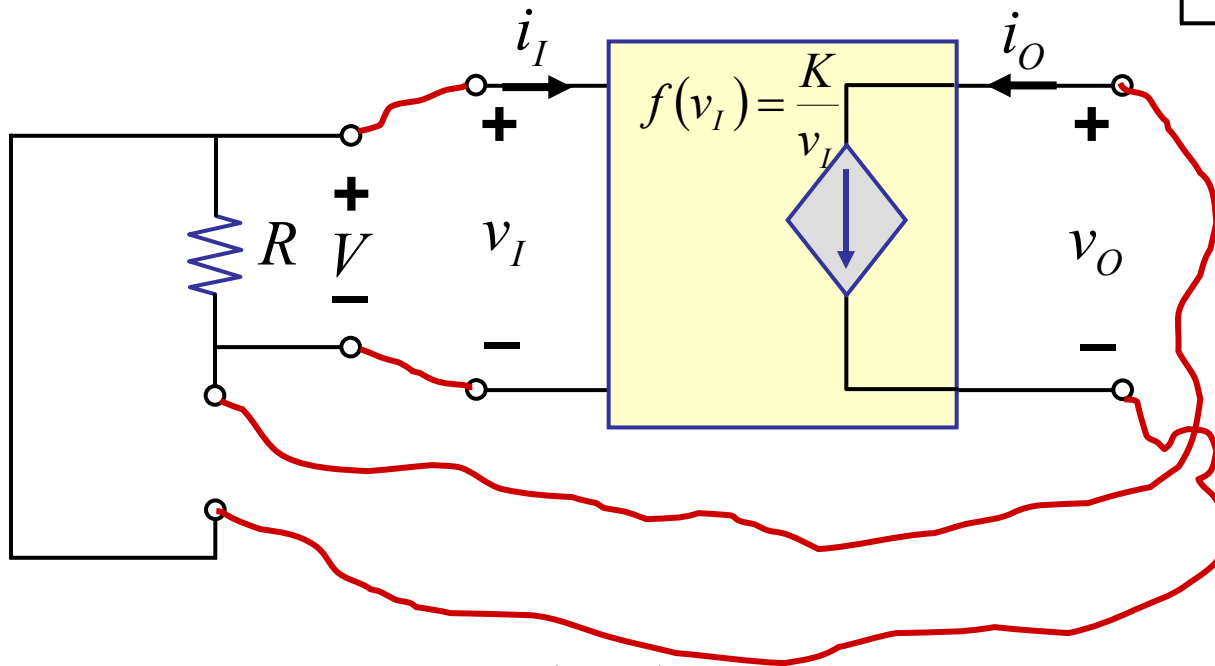
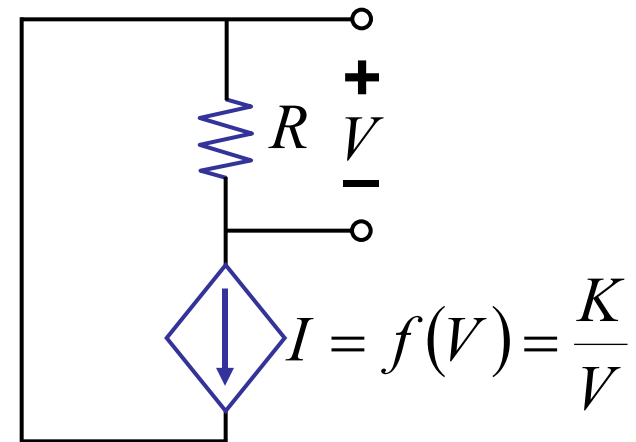


$$V =$$

Dependent Sources

■ Example 2 (dependent source): Find V

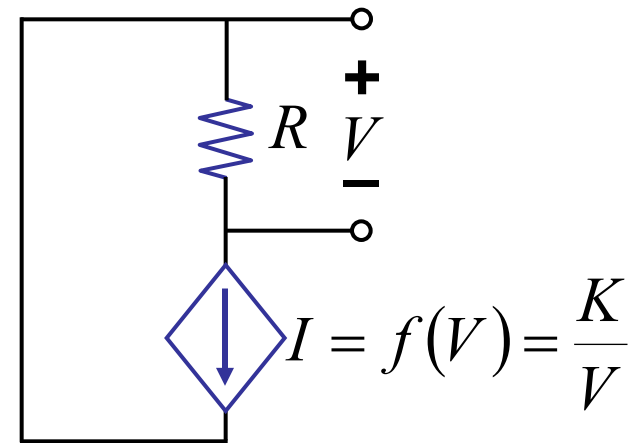
voltage
controlled
current
source



Dependent Sources

■ Example 2 (dependent source): Find V

voltage
controlled
current
source



e.g. $K = 10^{-3} \text{ Amp} \cdot \text{Volt}$
 $R = 1 \text{ k}\Omega$

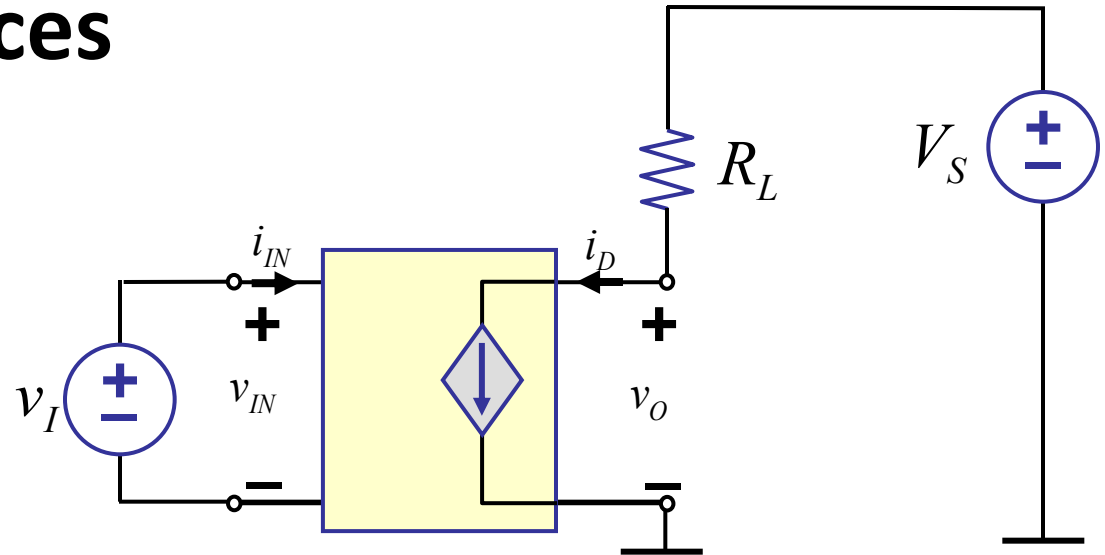
$$V = IR = \frac{K}{V} R$$

or $V^2 = KR$

or $V = \sqrt{KR}$
 $= \sqrt{10^{-3} \cdot 10^3}$
 $= 1 \text{ Volt}$

Dependent Sources

■ Example 3



$$i_D = f(v_{IN})$$

e.g. $i_D = f(v_{IN})$

$$= \frac{K}{2} (v_{IN} - 1)^2 \quad \text{for } v_{IN} \geq 1$$

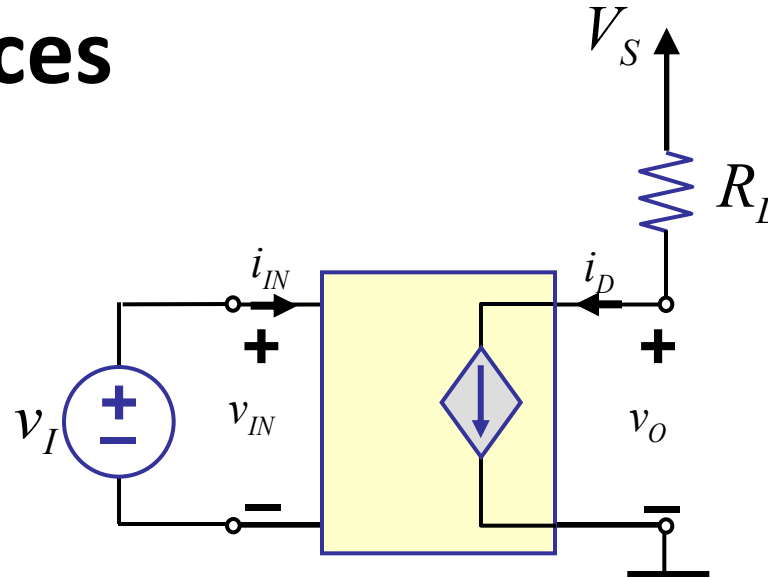
$$i_D = 0 \quad \text{otherwise}$$

(This is MOSFET
Switch-Current Source (SCS)
model with $V_T=1V...$)

Find v_O as a function of v_I .

Dependent Sources

■ Example 3



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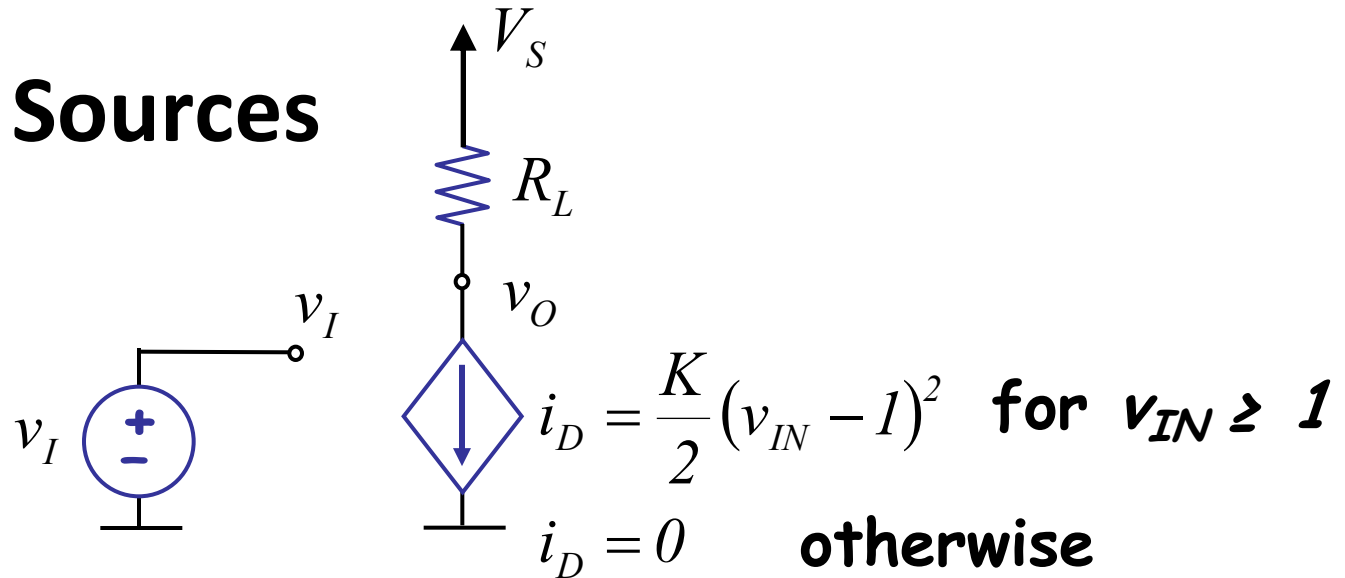
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Dependent Sources

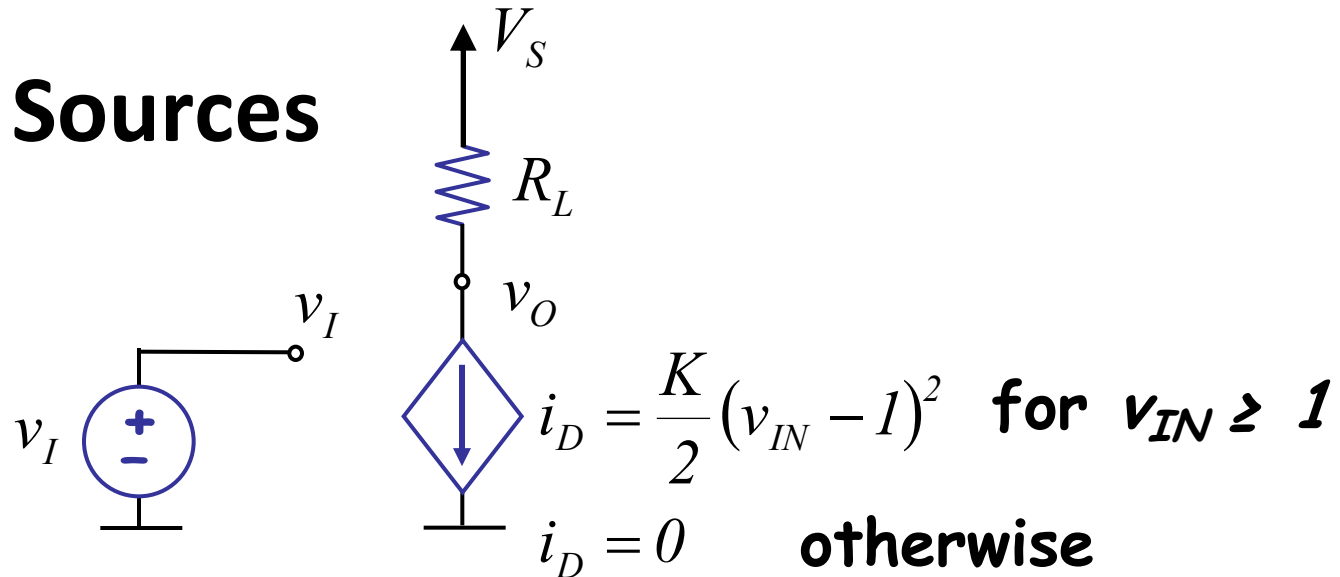
■ Example 3



Find v_O as a function of v_I .

Dependent Sources

■ Example 3



Find v_O as a function of v_I .

KVL

$$-V_S + i_D R_L + v_O = 0$$

$$v_O = V_S - i_D R_L$$



$$v_O = V_S - \frac{K}{2}(v_I - 1)^2 R_L \quad \text{for } v_I \geq 1$$

Hold that thought

$$v_O = V_S \quad \text{for } v_I < 1$$

Outline

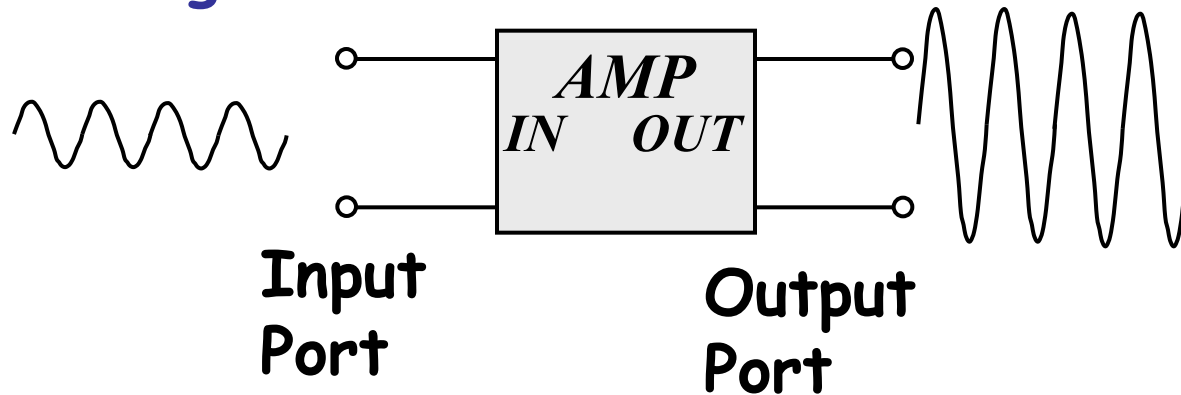
Textbook: 7.1, 7.2, 7.3, 7.4

- (Review of) Dependent Sources
- **Why Amplify?**
- **Signal Amplification**
- Actual MOSFET Characteristics
- MOSFET SCS Model

Why Amplify?

Signal amplification key to both analog and digital processing.

Analog:

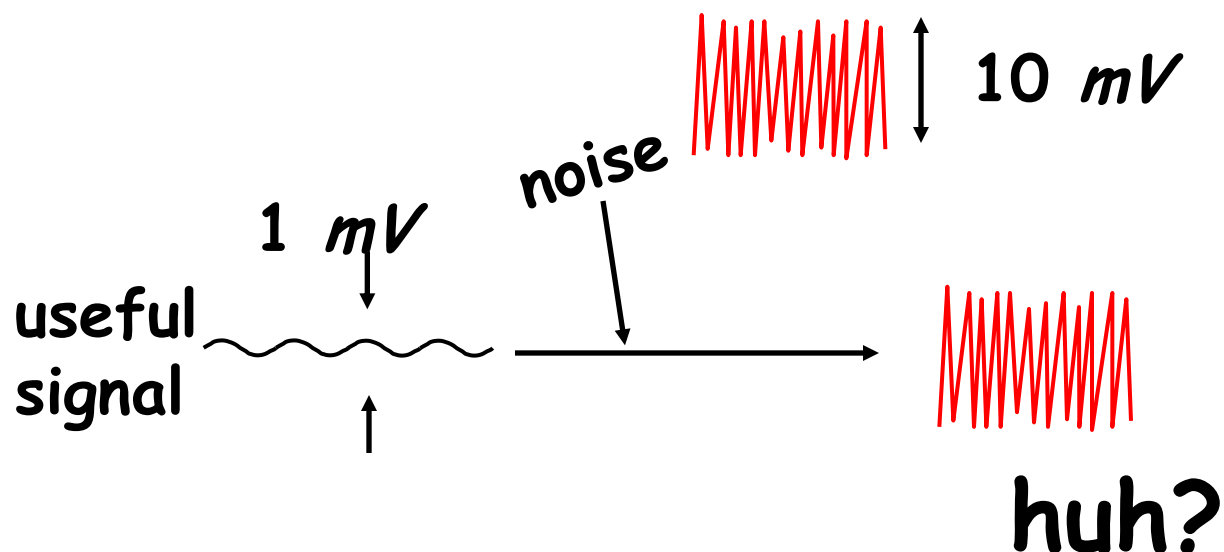


Besides the obvious advantages of being heard farther away, amplification is key to noise tolerance during communication

Why Amplify?

Amplification is key to noise tolerance during communication

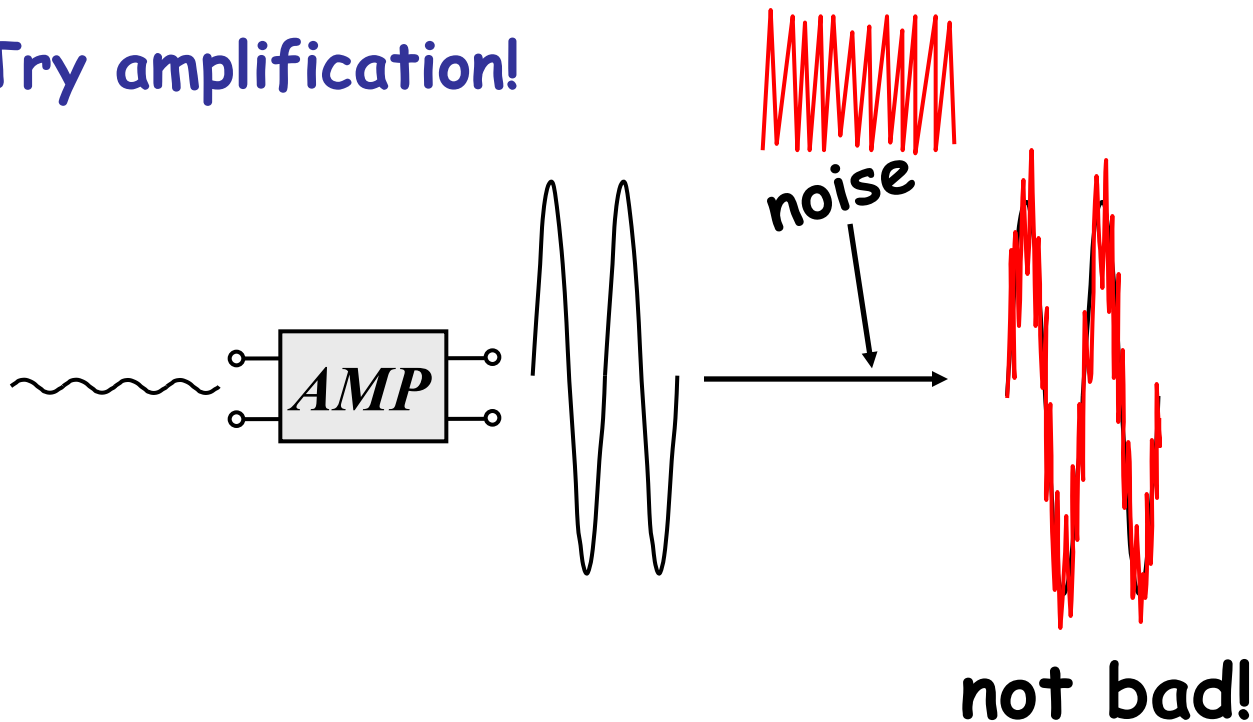
No amplification



Why Amplify?

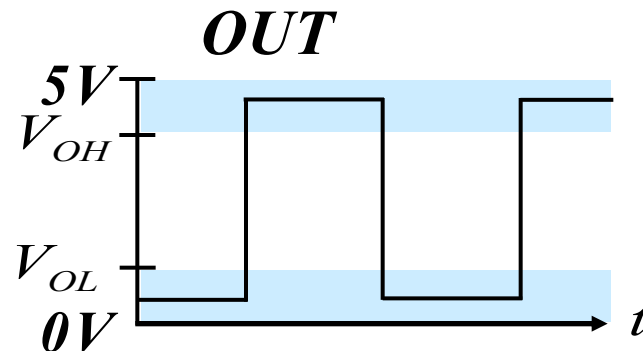
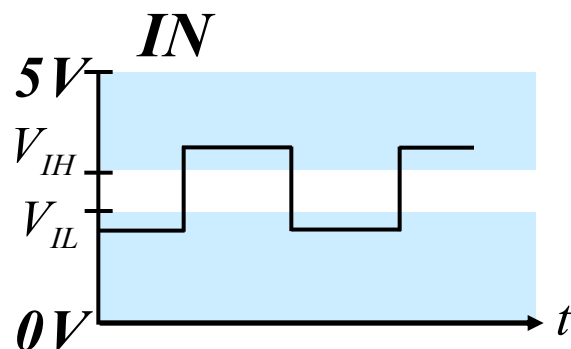
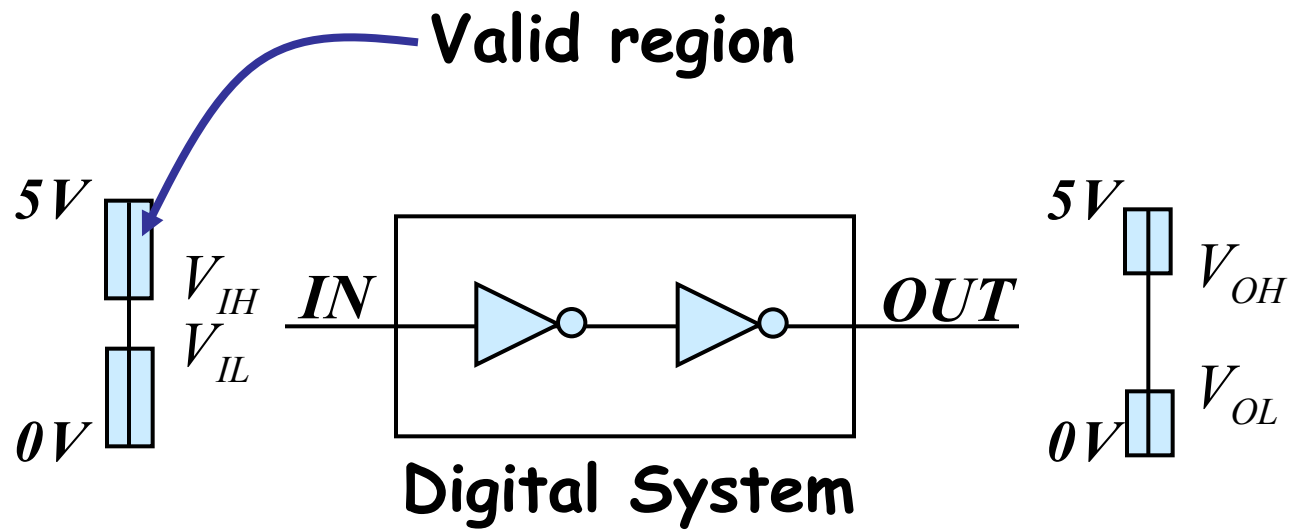
Amplification is key to noise tolerance during communication

Try amplification!



Why Amplify?

Digital:

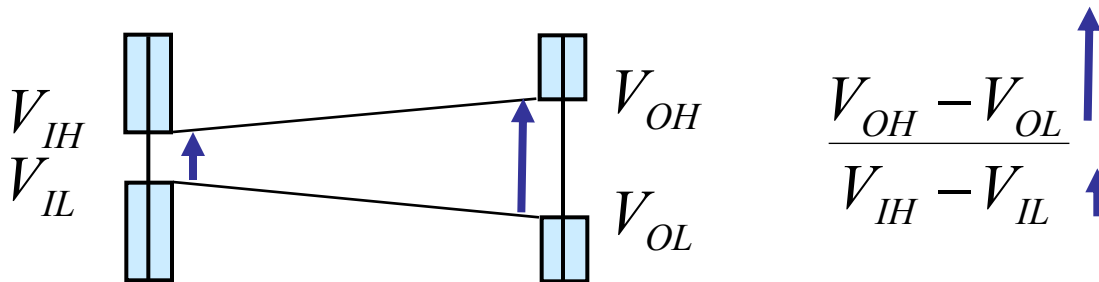


Why Amplify?

Digital:

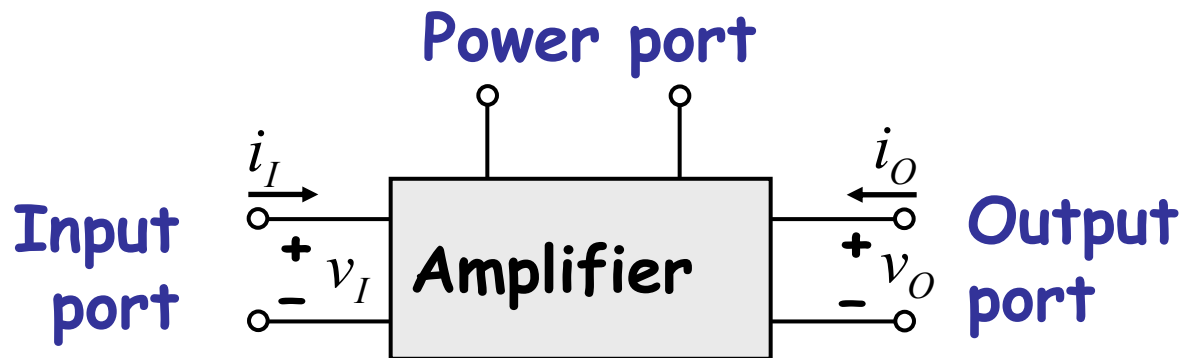
Static discipline requires amplification!

Minimum amplification (gain) needed:



Signal Amplification

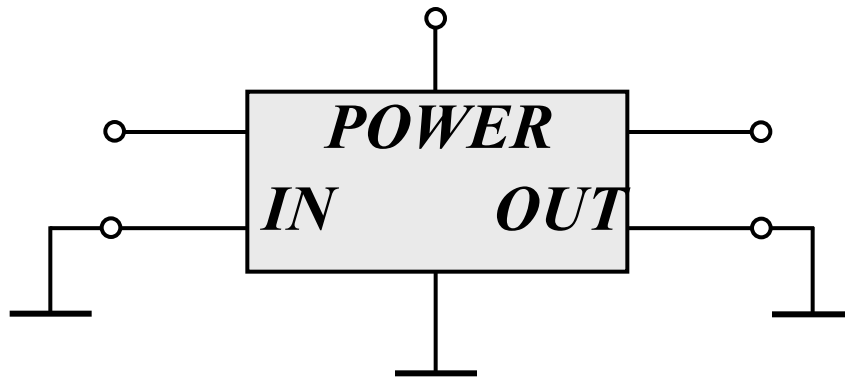
An amplifier is a 3-ported device, actually



We often don't show the power port.

Signal Amplification

An amplifier is a 3-ported device, actually



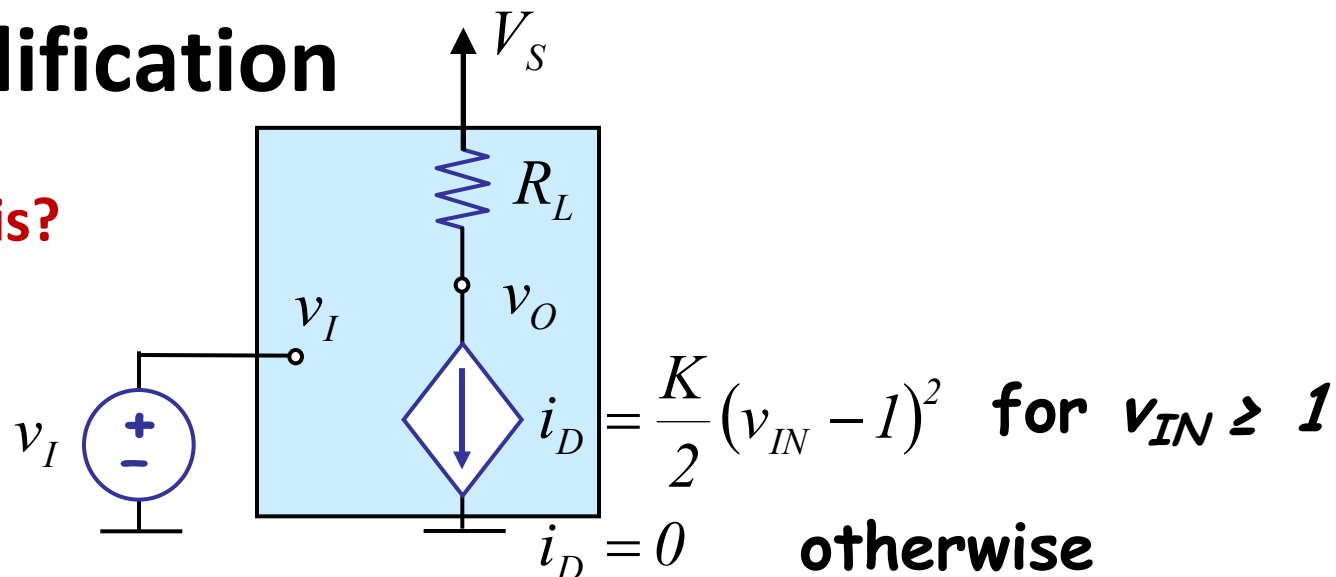
Also, for convenience we commonly observe “the common ground discipline.”

In other words, all ports often share a common reference point called “ground.”

How do we build one?

Signal Amplification

■ Remember this?



Find v_O as a function of v_I .

KVL

Claim:
This is an amplifier!

$$-V_S + i_D R_L + v_O = 0$$

$$v_O = V_S - i_D R_L$$



$$v_O = V_S - \frac{K}{2}(v_I - 1)^2 R_L \quad \text{for } v_I \geq 1$$

$$v_O = V_S \quad \text{for } v_I < 1$$

Signal Amplification

So, where's the amplification?

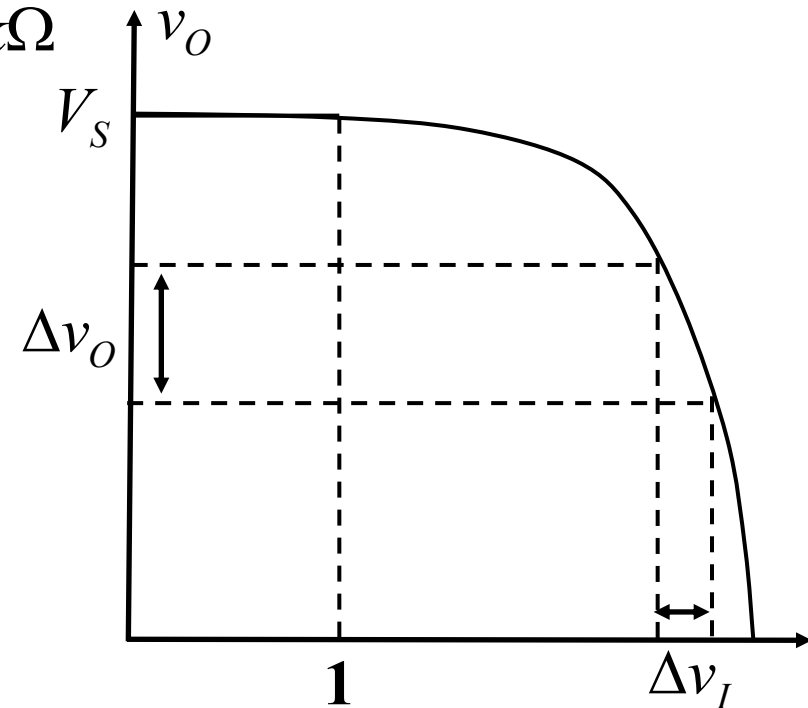
Let's look at the v_O versus v_I curve.

e.g. $V_S = 10V$, $K = 2 \frac{mA}{V^2}$, $R_L = 5k\Omega$

$$v_O = V_S - \frac{K}{2} R_L (v_I - 1)^2$$

$$= 10 - \frac{\cancel{2}}{\cancel{2}} \cdot \cancel{10}^{-3} \cdot 5 \cdot \cancel{10}^3 (v_I - 1)^2$$

$$v_O = 10 - 5 (v_I - 1)^2$$



$$\frac{\Delta v_O}{\Delta v_I} > 1 \rightarrow \text{amplification}$$

Signal Amplification

So, where's the amplification?

Plot v_O versus v_I

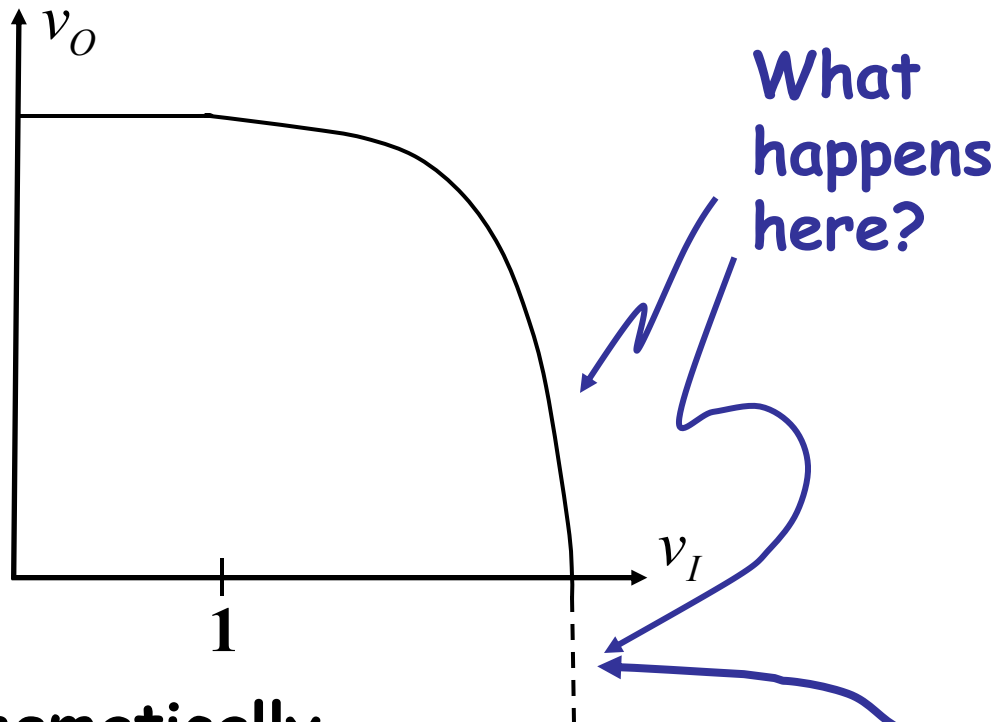
$$v_O = 10 - 5(v_I - 1)^2$$

		v_I	v_O		
		0.0	10.00		
		1.0	10.00		
		1.5	8.75		
0.1 change in v_I		2.0	5.00	1V change in v_O	
		2.1	4.00		
		2.2	2.80		
		2.3	1.50		
		2.4	~ 0.00		

Gain!

Signal Amplification

One nit ...



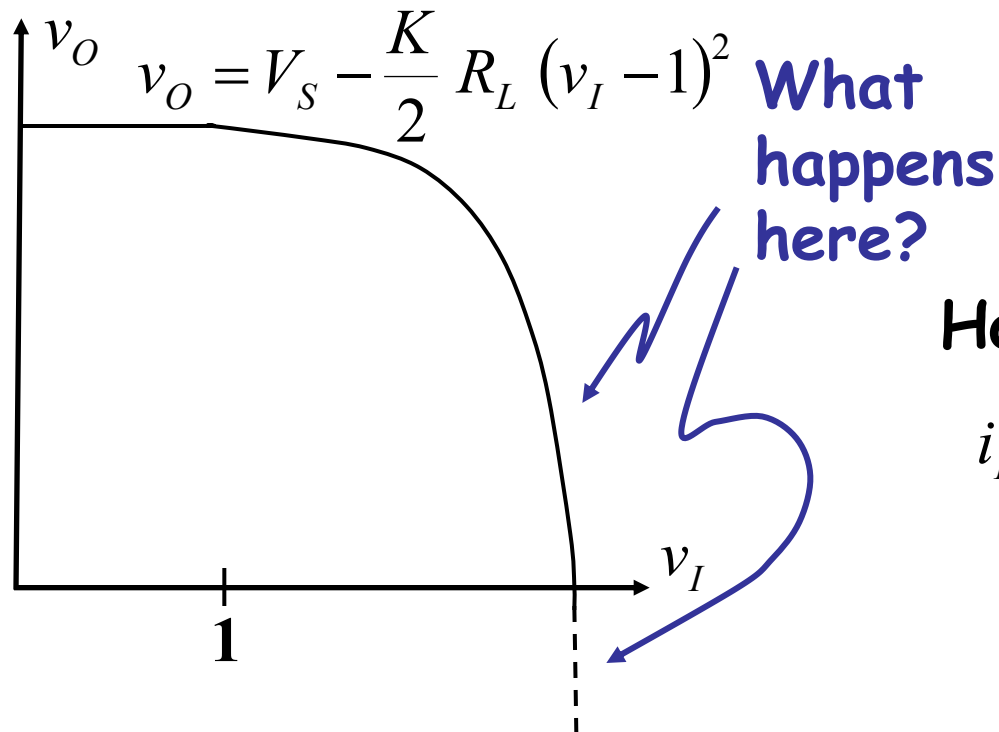
Mathematically,

$$v_O = V_S - \frac{K}{2} R_L (v_I - 1)^2$$

So is mathematically predicted behavior

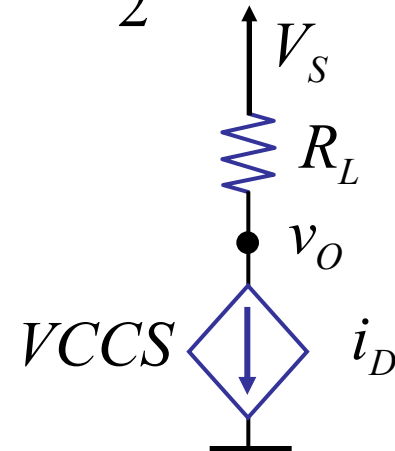
Signal Amplification

One nit ...



However, from

$$i_D = \frac{K}{2} (v_I - 1)^2 \quad \text{for } v_I \geq 1$$

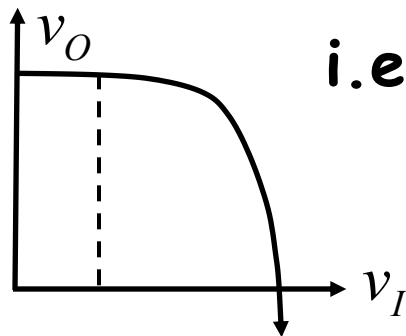


For $v_O > 0$, $VCCS$ consumes power: $v_O i_D$
 For $v_O < 0$, $VCCS$ must supply power!

Signal Amplification

One nit ...

If VCCS were a device that can source power, then the mathematically predicted behavior could be observed —



i.e.
$$v_O = V_S - \frac{K}{2} R_L (v_I - 1)^2$$

where v_O goes *negative*

Signal Amplification

One nit ...

If VCCS is a passive device,
then it cannot source power,
so v_O cannot go negative.

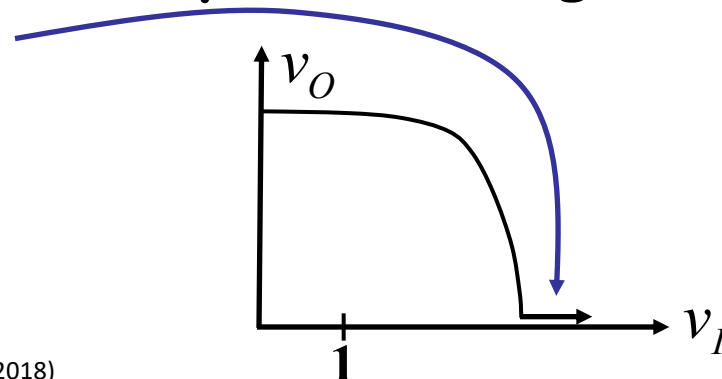
Turns out, our model breaks down.

Commonly
$$i_D = \frac{K}{2} (v_I - 1)^2$$

will no longer be valid when $v_O \leq 0$.

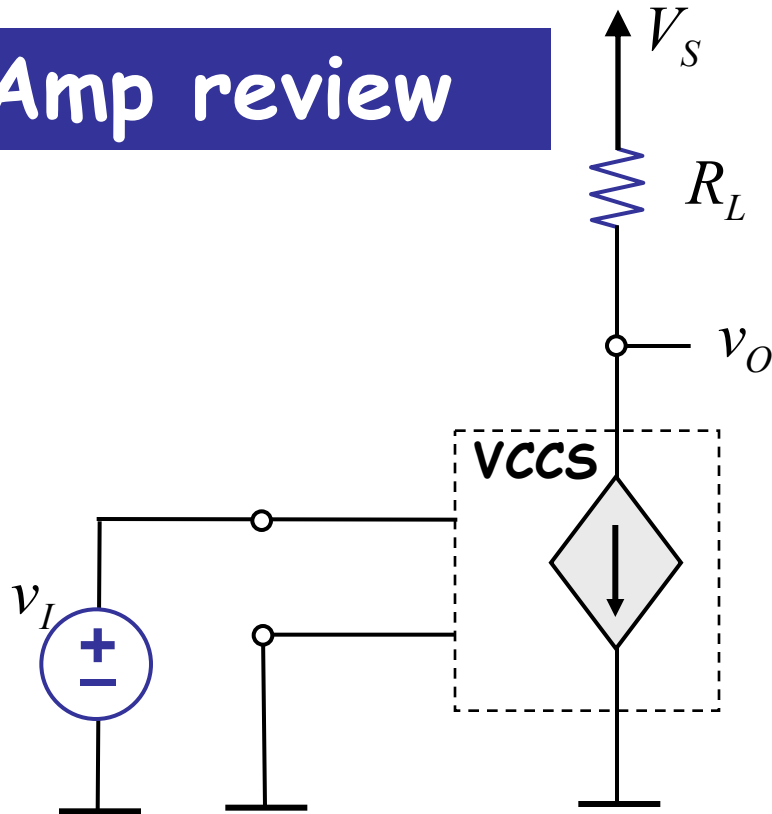
e.g. i_D saturates (stops increasing)

and we observe:



Signal Amplification

Amp review



$$i_D = \frac{K}{2}(v_I - 1)^2 \quad \text{for } v_I \geq 1V$$

$$= 0 \quad \text{otherwise}$$

$$v_O = V_S - i_D R_L$$

$$\frac{K}{2}(v_I - 1)^2$$

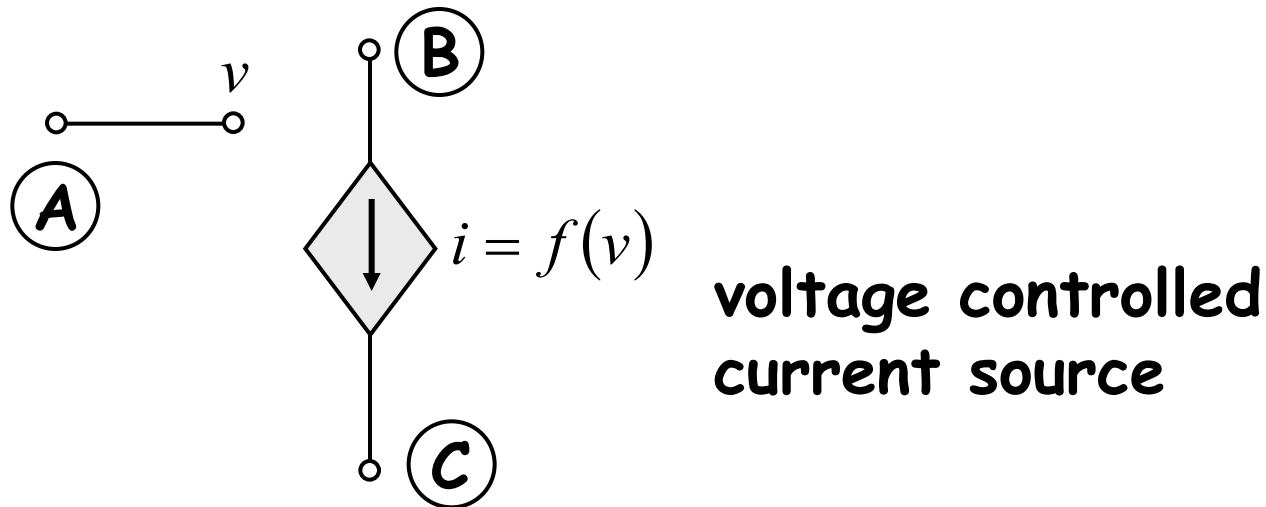
Outline

Textbook: 7.1, 7.2, 7.3, 7.4

- (Review of) Dependent Sources
- Why Amplify?
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- **Actual MOSFET Characteristics**
- **MOSFET SCS Model**

Actual MOSFET Characteristics

Key device Needed:



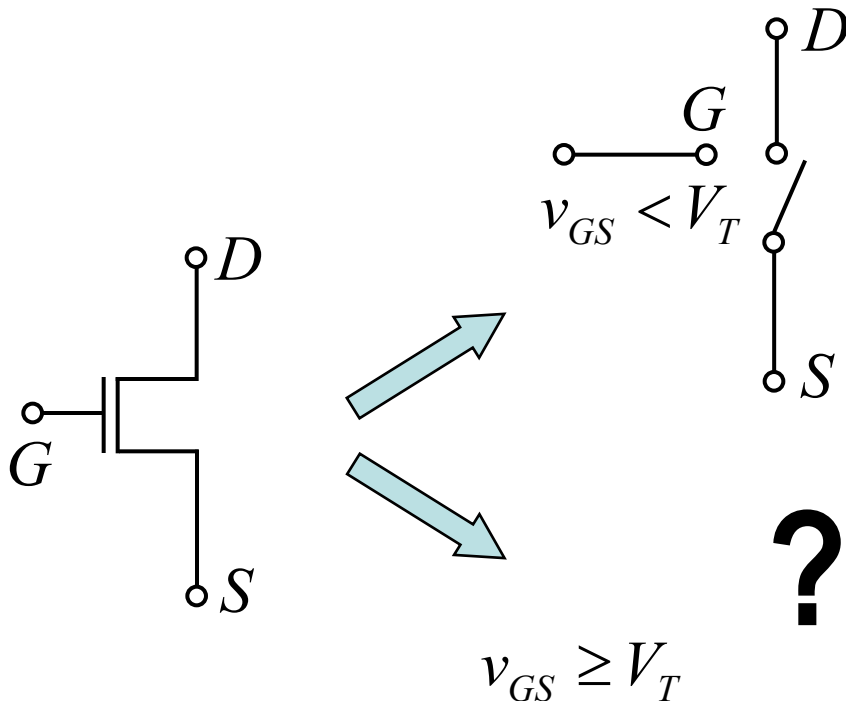
Let's look at our old friend, the MOSFET ...

Actual MOSFET Characteristics

Key device Needed:

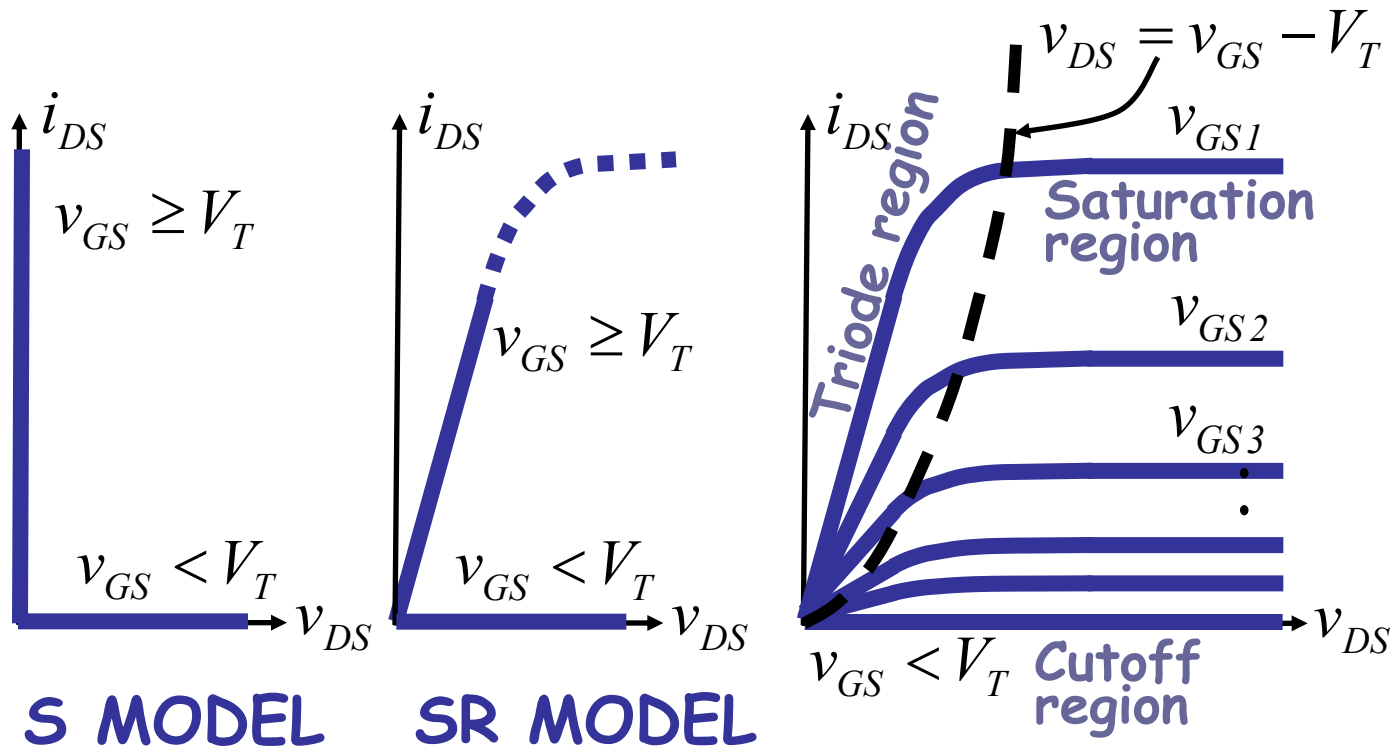
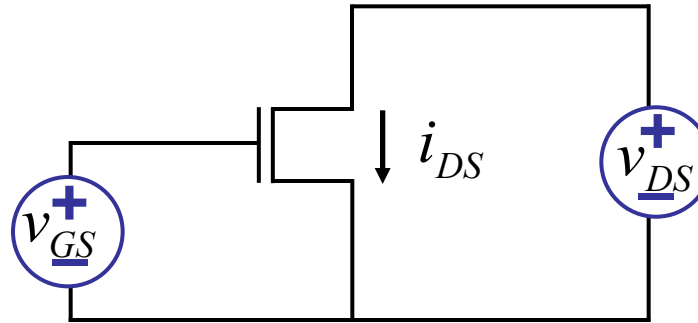
Our old friend, the MOSFET ...

First, we sort of lied. The on-state behavior of the MOSFET is quite a bit more complex than either the ideal switch (S) or the resistor (SR) model.



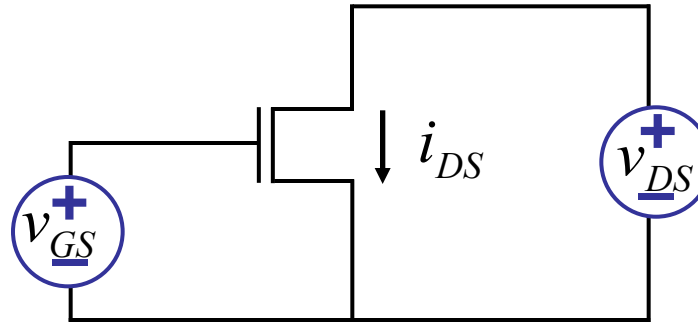
Actual MOSFET Characteristics

Graphically



Actual MOSFET Characteristics

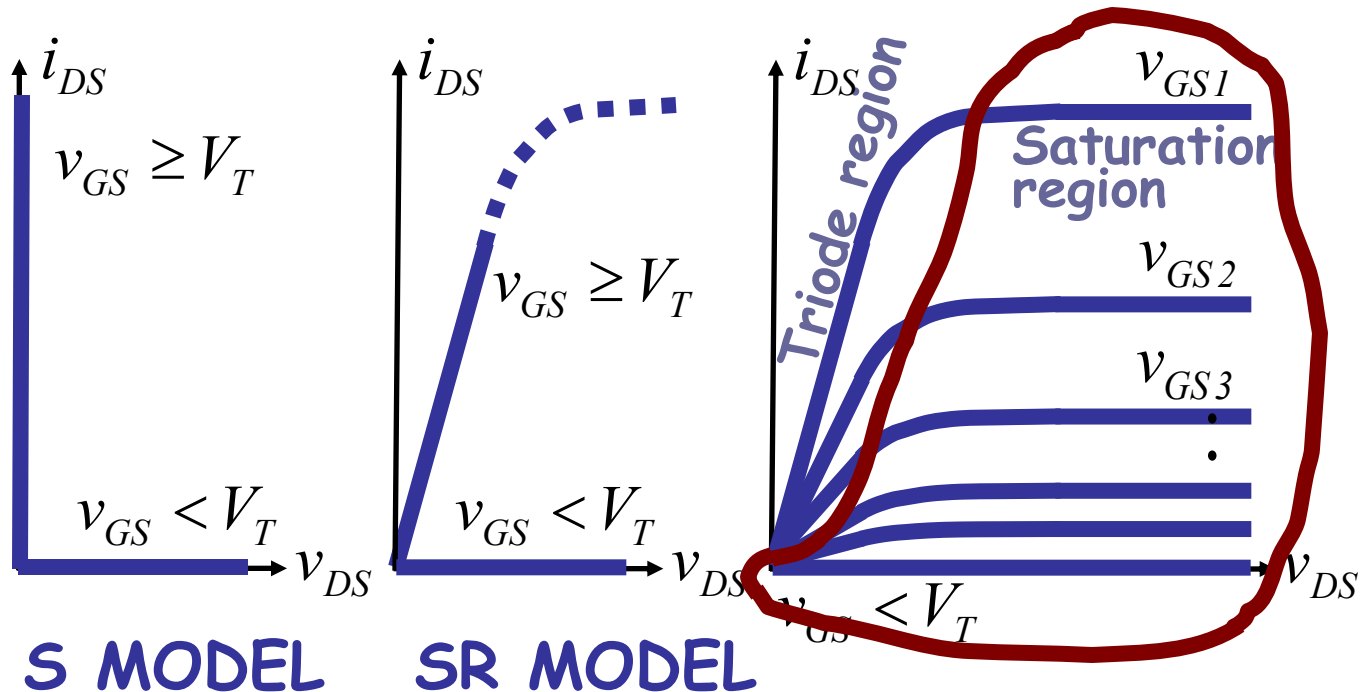
Graphically



when

$$v_{DS} \geq v_{GS} - V_T$$

Notice that
MOSFET
behaves like a
current source

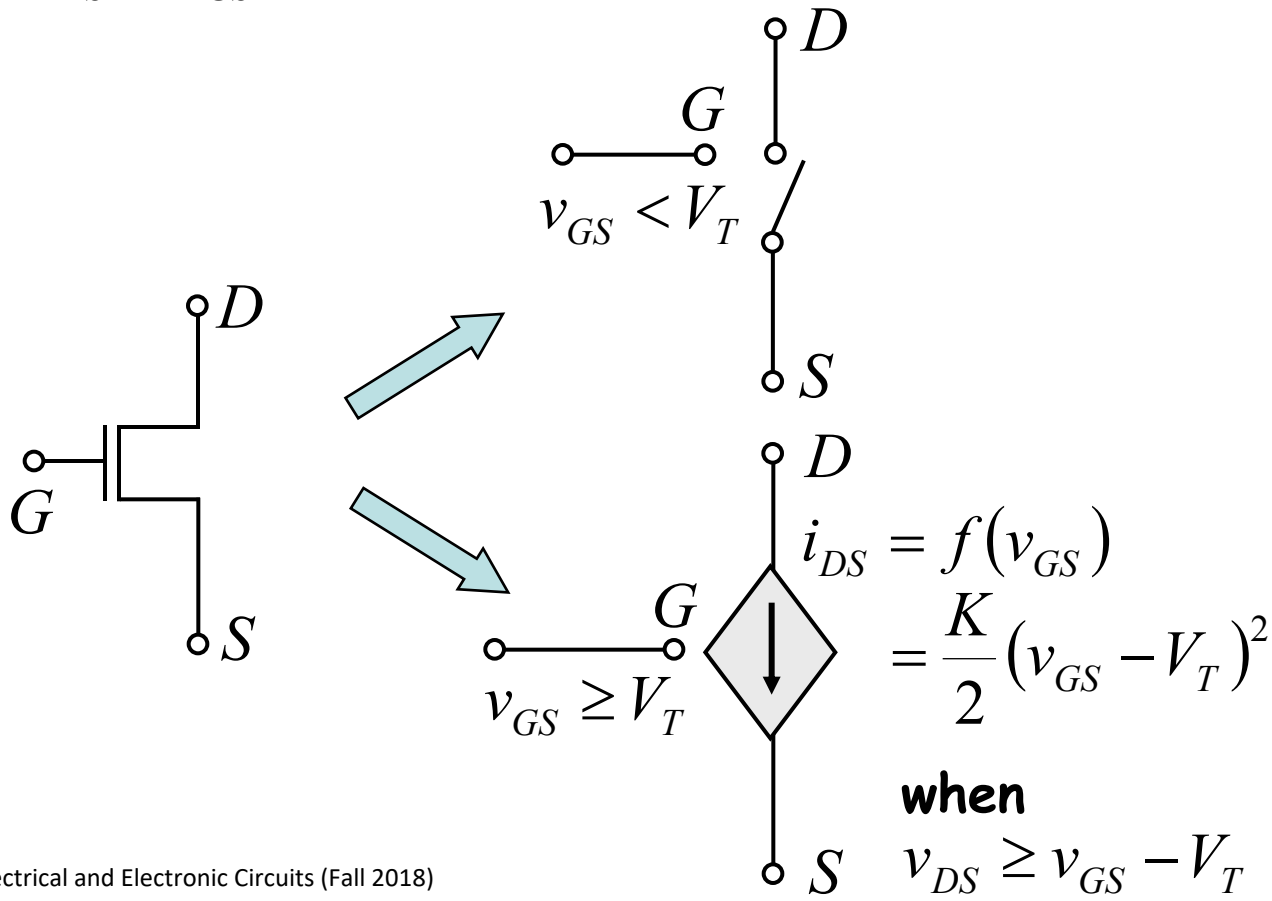


MOSFET SCS Model

■ SCS Model: Switched Current Source Model

- Saturation region of operation: “saturation principle”

When $v_{DS} \geq v_{GS} - V_T$



MOSFET SCS Model

■ Reconciling the models

